

Proiect

2020/2021

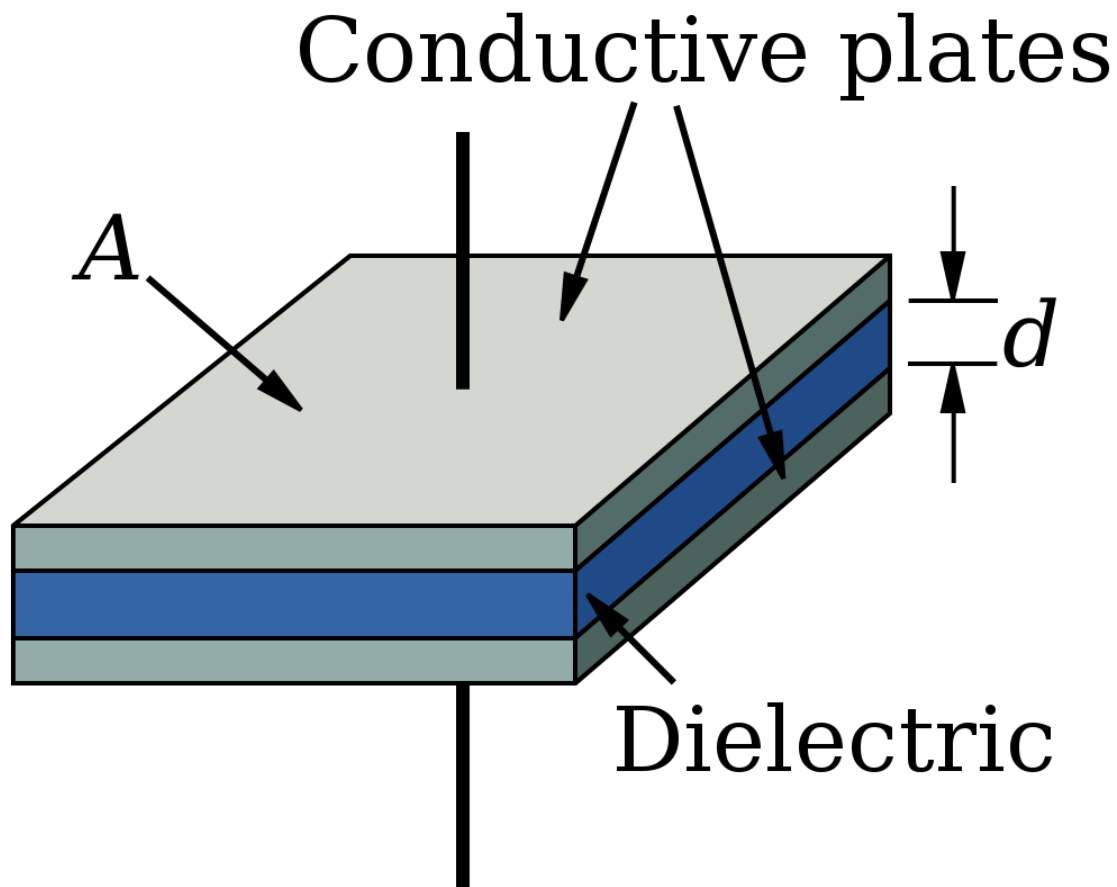
# Circuite Integrate Monolitice pentru Microunde

# Tema proiect

individuala

# Condensator planar

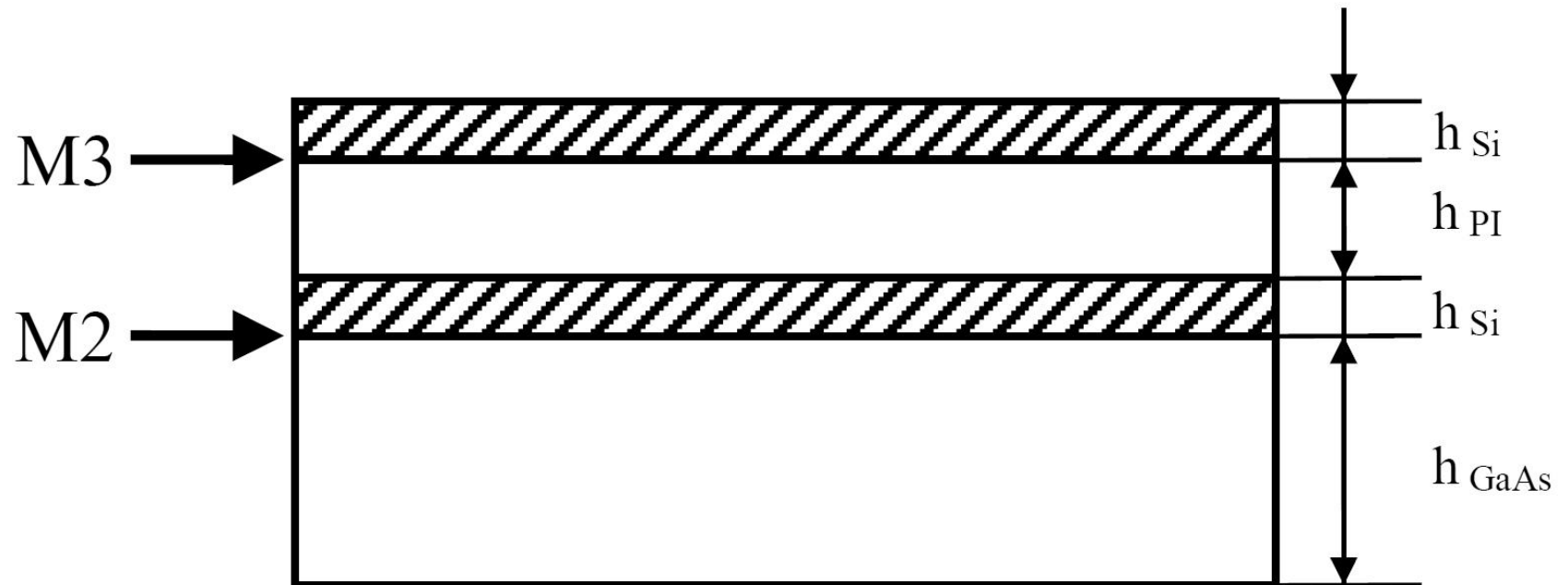
- doua armaturi plane paralele



$$C = \frac{\varepsilon \cdot A}{d}$$

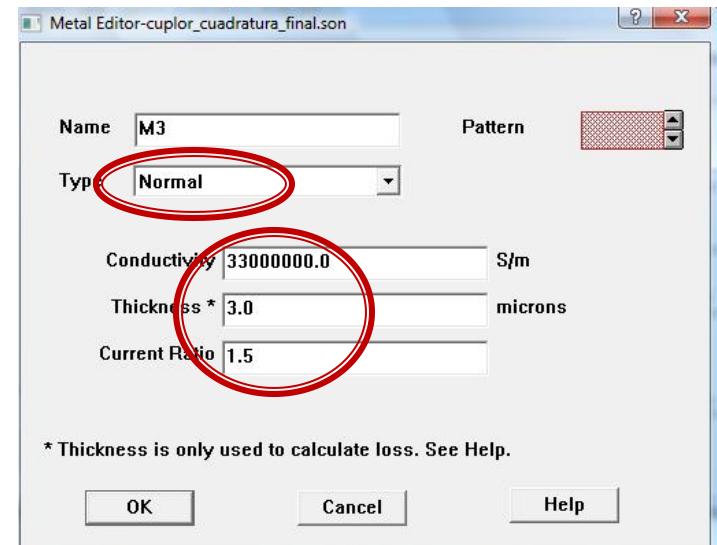
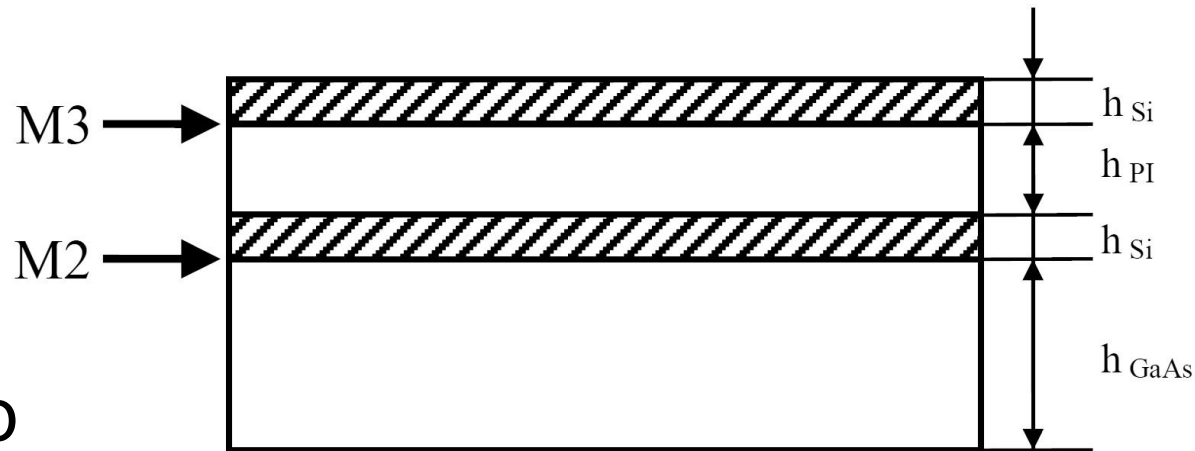
# Realizare

- structura tehnologiei (foundry) Plessey



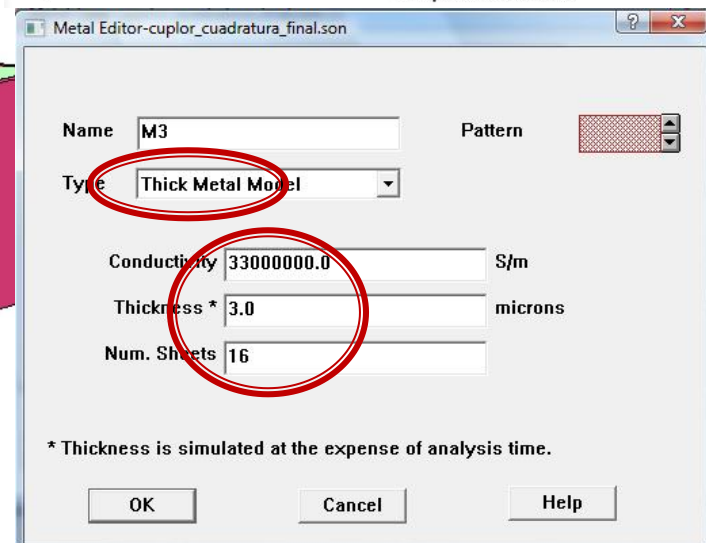
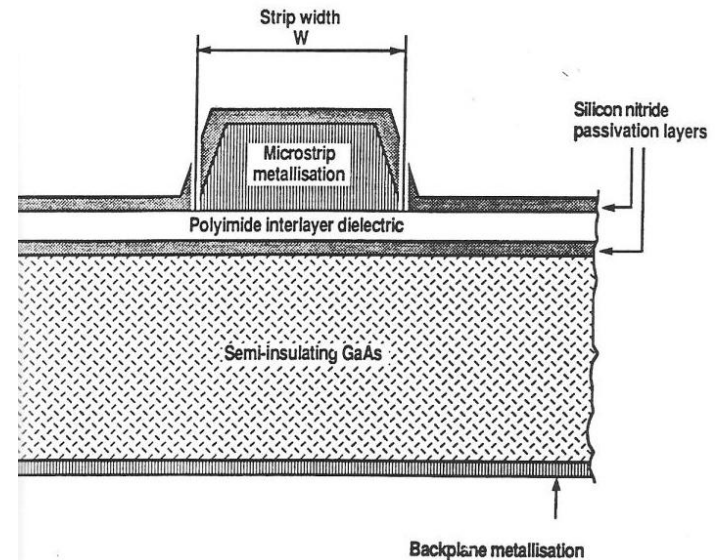
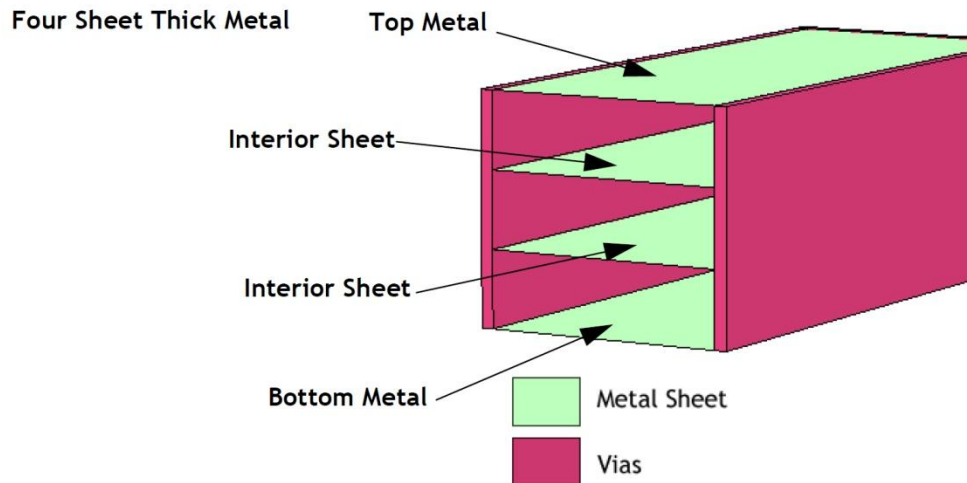
# Modelare

- Structuri
  - cu 3 straturi
  - cu 5 straturi
- Metalizare  $h=0$ 
  - Ideal
  - Normal



# Modelare supliment

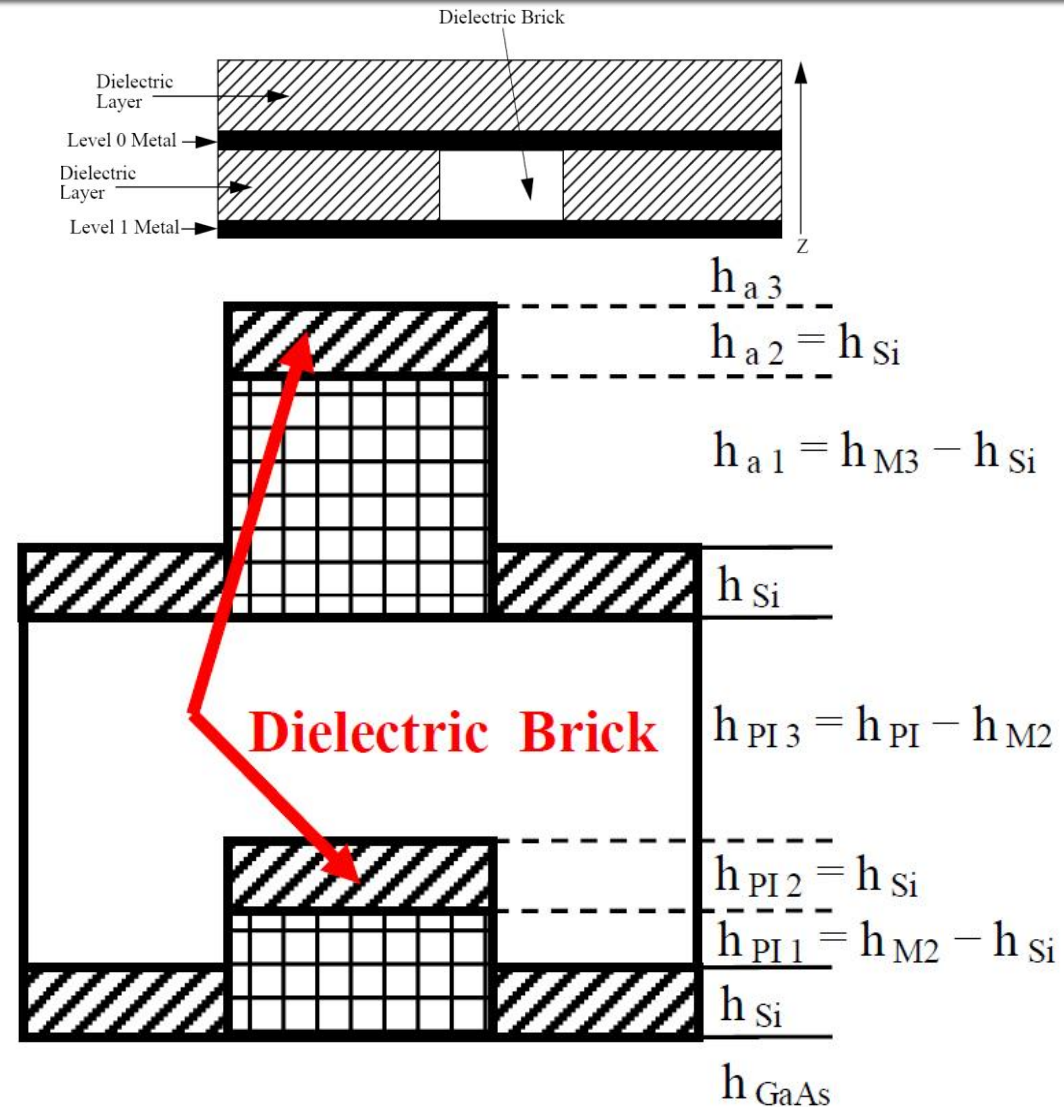
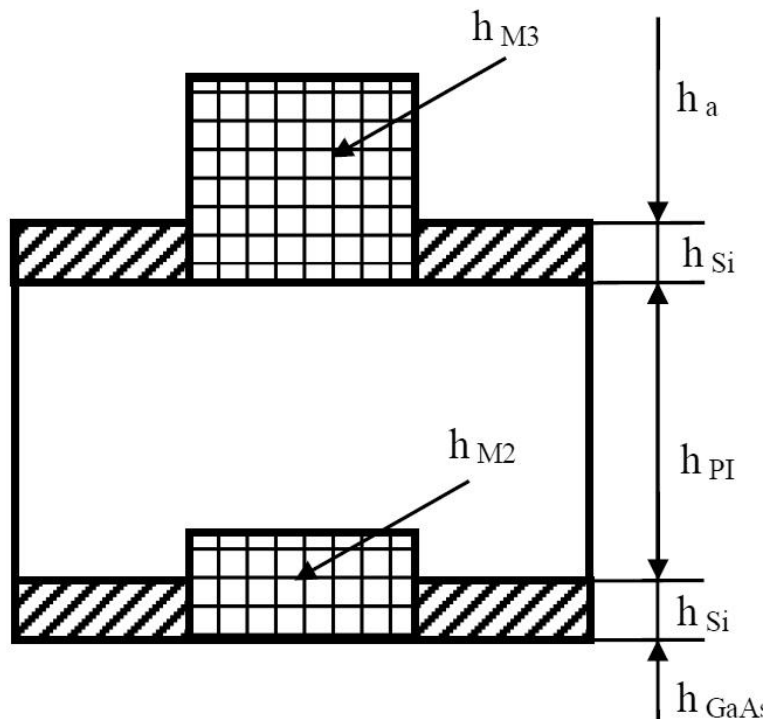
- Structuri
  - cu 9 straturi
- Metalizare  $h \neq 0$ 
  - Thick



# Modelare supliment

## ■ Structuri

- cu 5 -> 9+ straturi



# Parametri

Nr.	Material	$\epsilon_r$	$\tan \delta$	$\sigma[\text{S/m}]$	$R_{sq}[\text{m}\Omega/\text{sq}]$	$h[\mu\text{m}]$
1	GaAs	12.85	$0.3 \cdot 10^{-3}$			200
2	$\text{Si}_3\text{N}_4$	7.2	$15 \cdot 10^{-3}$			0.13
3	PI	3.4	$55 \cdot 10^{-3}$			1.8
4	M2			$3.6 \cdot 10^7$	55	0.5
5	M3			$3.3 \cdot 10^7$	10	3

$$R = \frac{\rho \cdot l}{S} = \frac{l}{\sigma \cdot w \cdot h} = \frac{1}{\sigma \cdot h} \cdot \frac{l}{w} = R_{sq} \cdot \frac{l}{w} \quad l = w \rightarrow R = R_{sq}$$

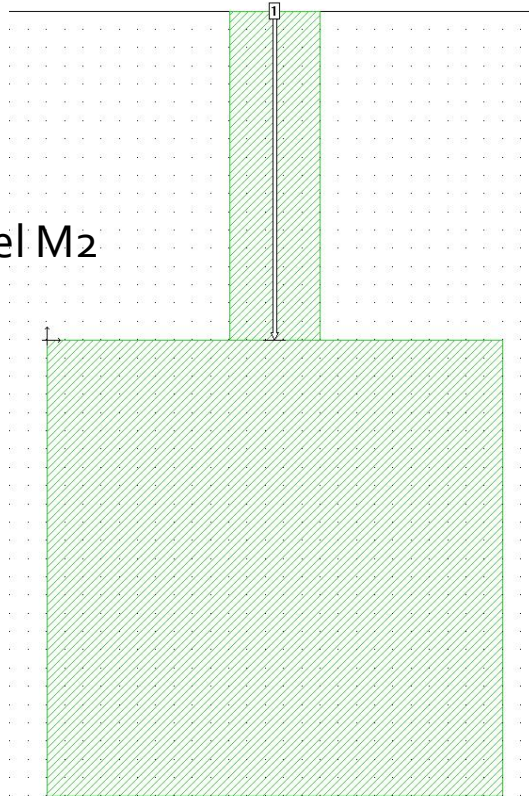


# Simulare

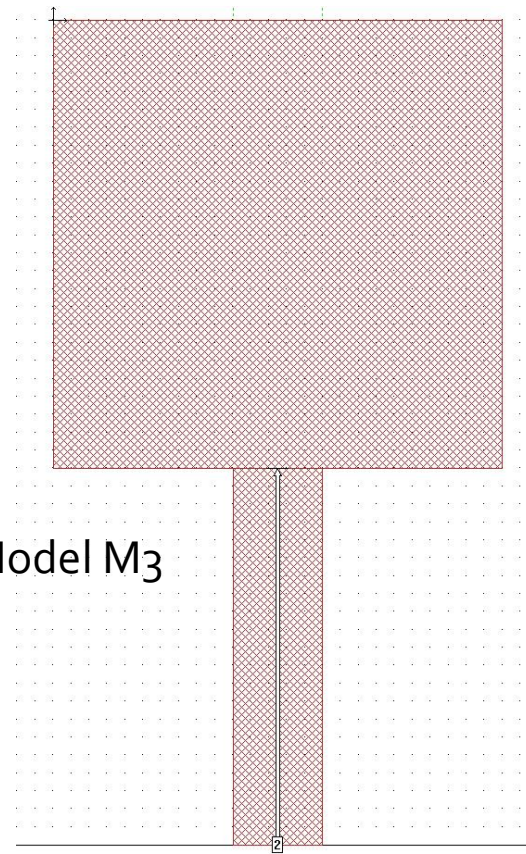
# Modelare

- Linii de  $50\Omega$
- Reference plane

Model M2

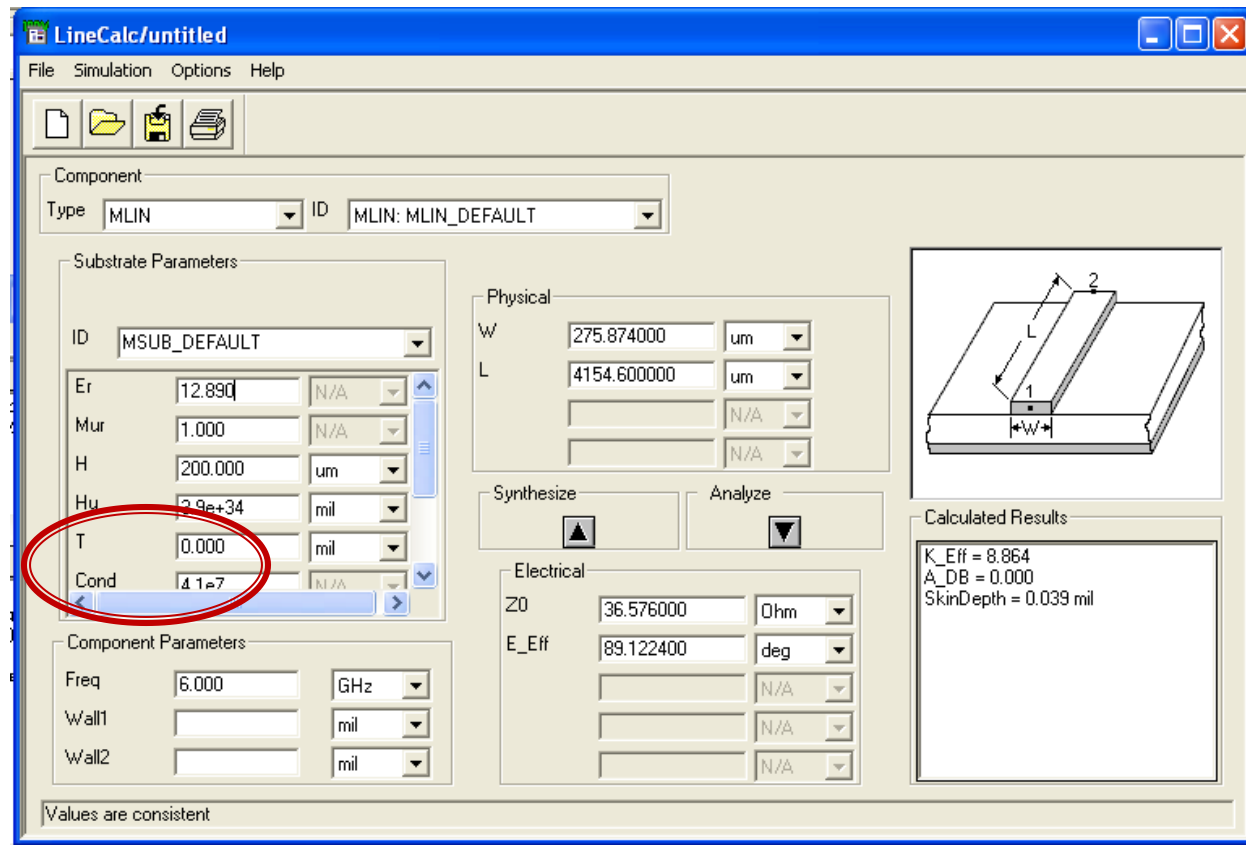


Model M3



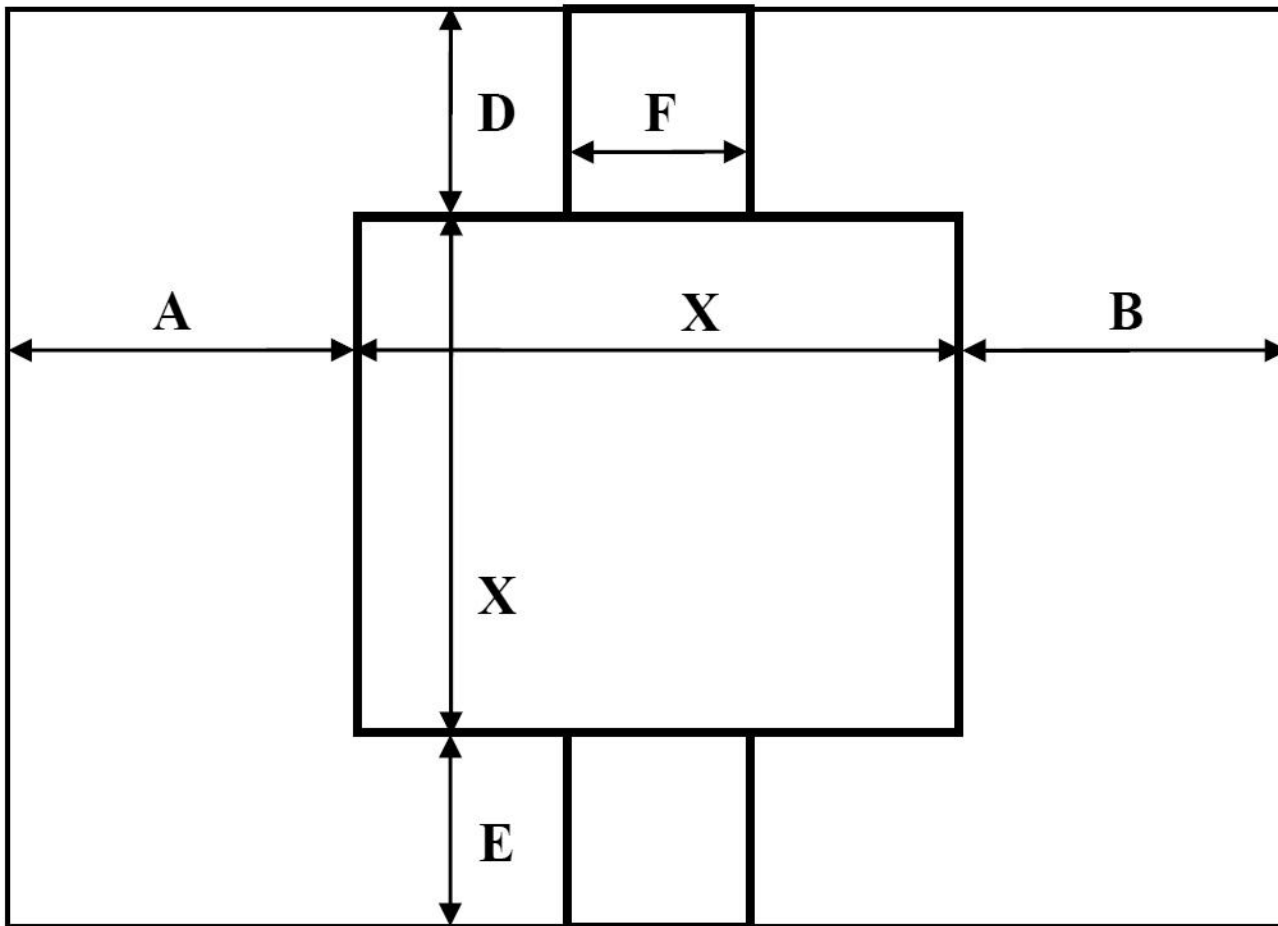
# Modelare

- Linii de  $50\Omega$  -> Linecalc
- Thickness/Conductivity



# Dimensionare

## ■ Box Size/Cell Size



$$X = m \cdot \Delta x$$

$$X = n \cdot \Delta y$$

$$\Delta x = \Delta y$$

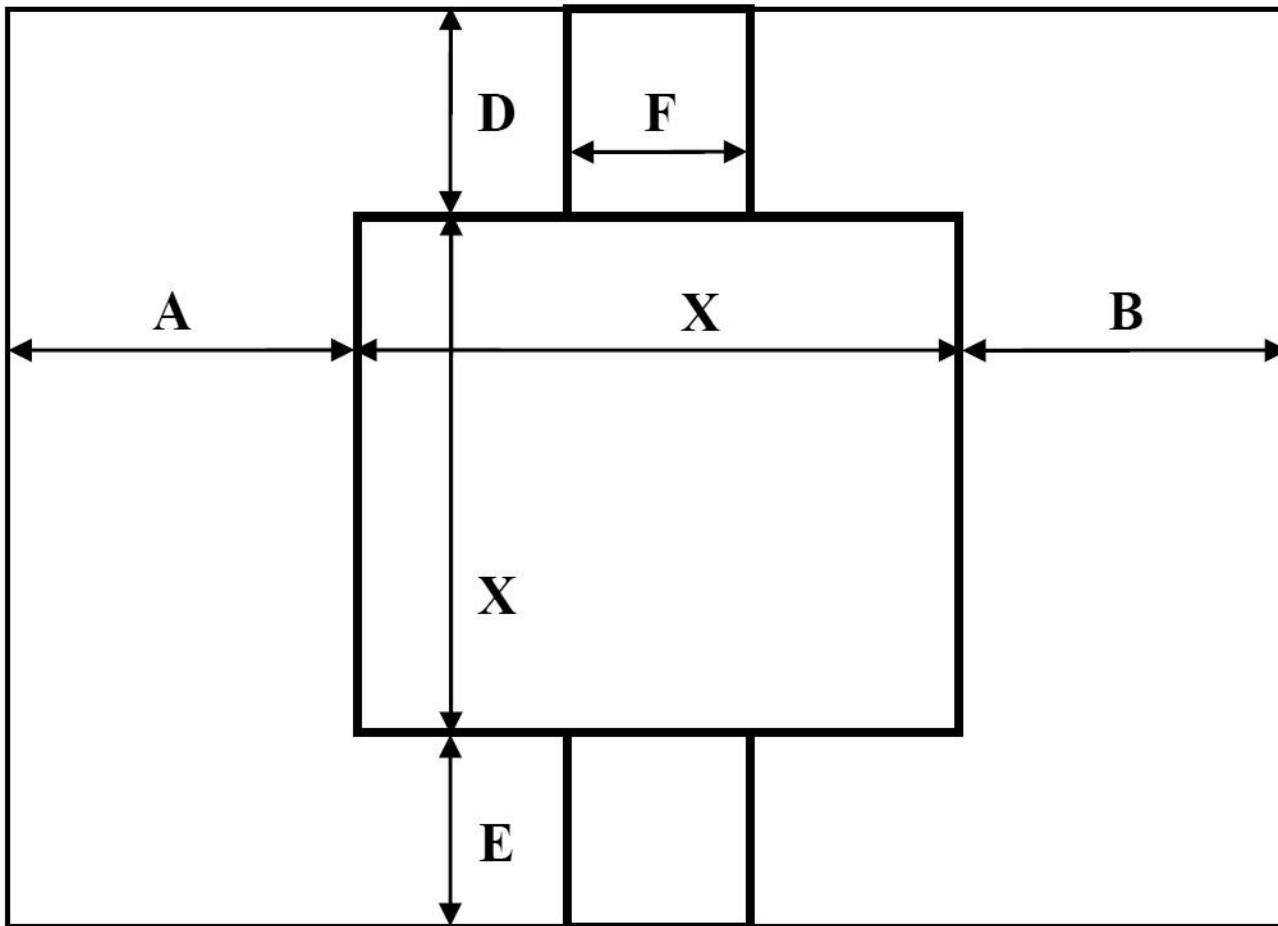
$$m = n = 2^p$$

$$W = H = 2 \cdot X$$

$$W = H = 2^{p+1} \cdot \Delta x$$

# Dimensionare

## ■ Box Size/Cell Size



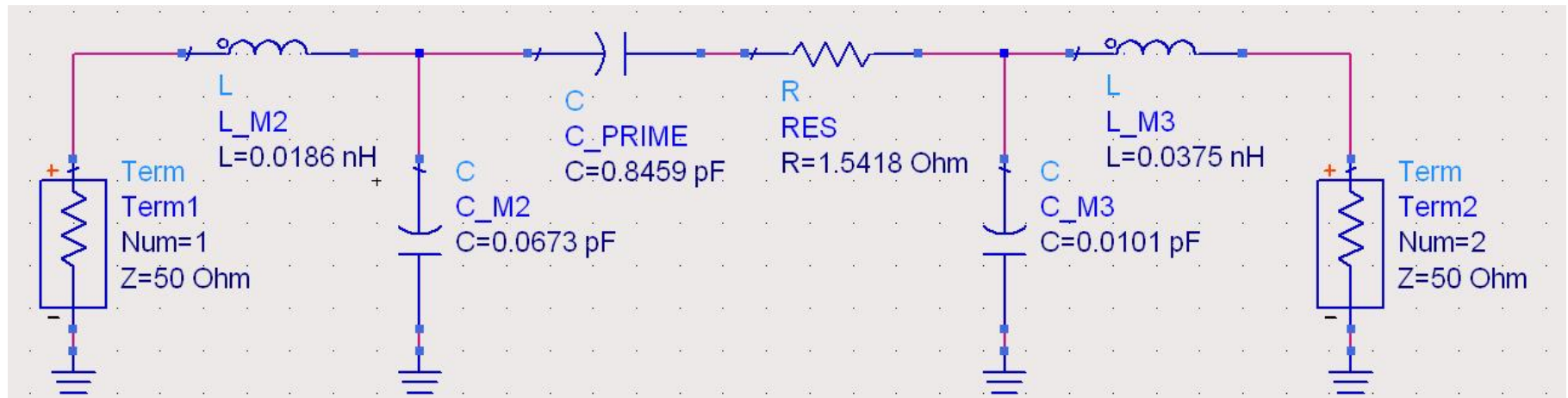
$$F \approx s \cdot \Delta x$$
$$\Delta x = \Delta y$$

$$F \neq s \cdot \Delta x$$
$$\Delta x = \Delta y / 2, 4, 8$$

# Circuit echivalent

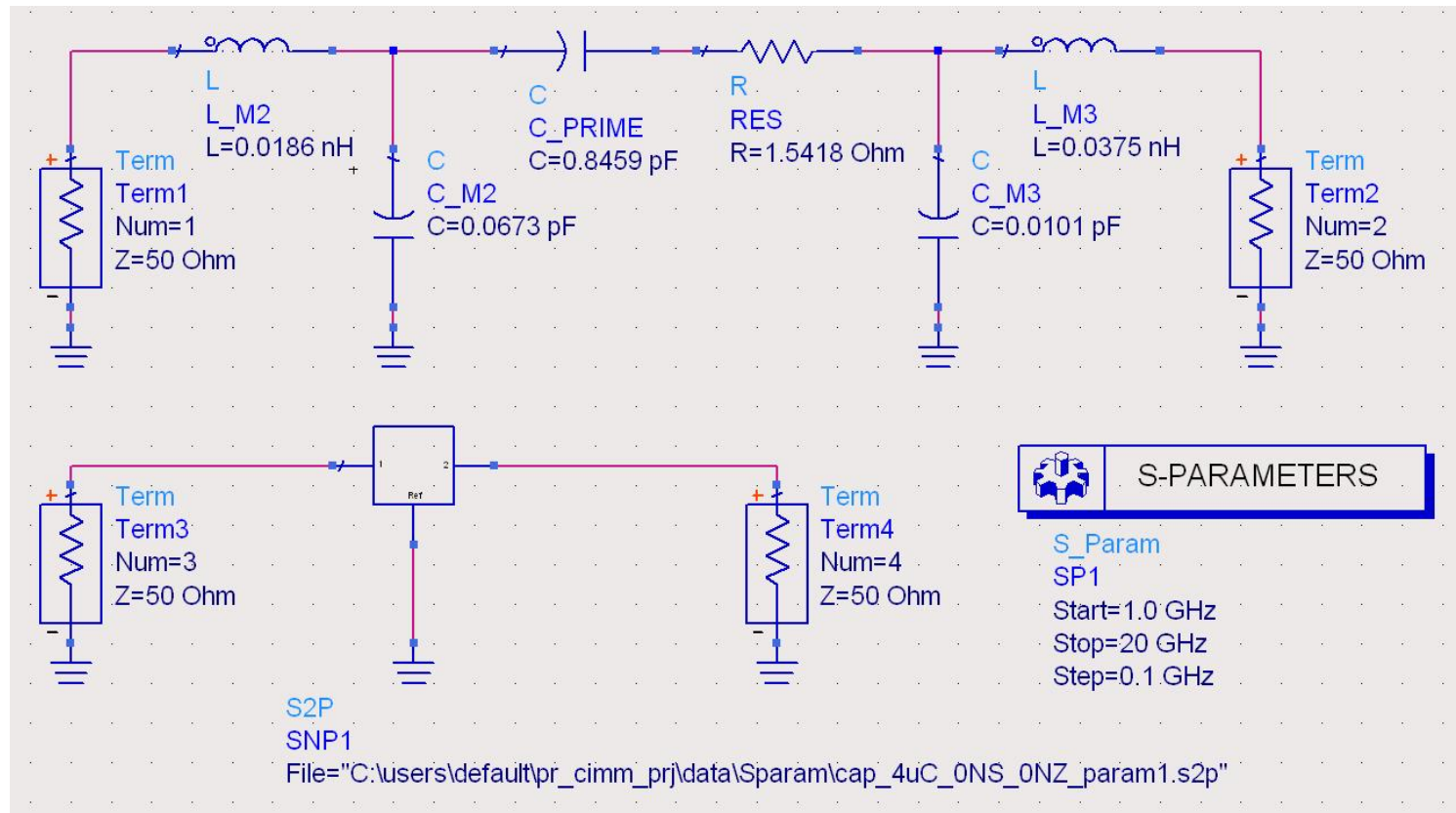
# Circuit echivalent

- Sonnet ofera parametrii S
- Schema echivalenta e schema care ofera aceeasi parametri S
- Curs: Schema + Relatii de calcul valori



# Circuit echivalent

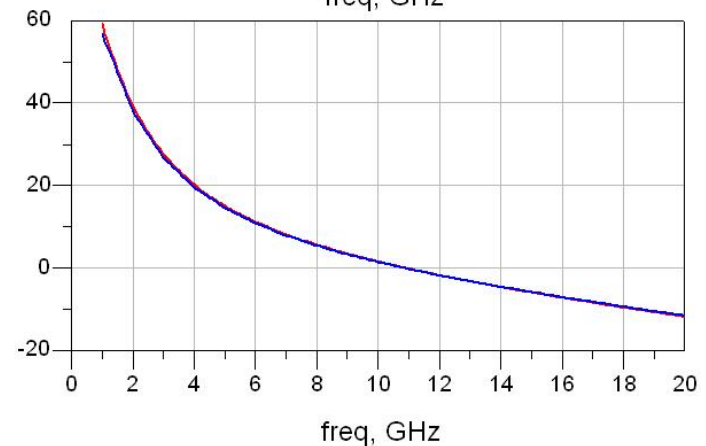
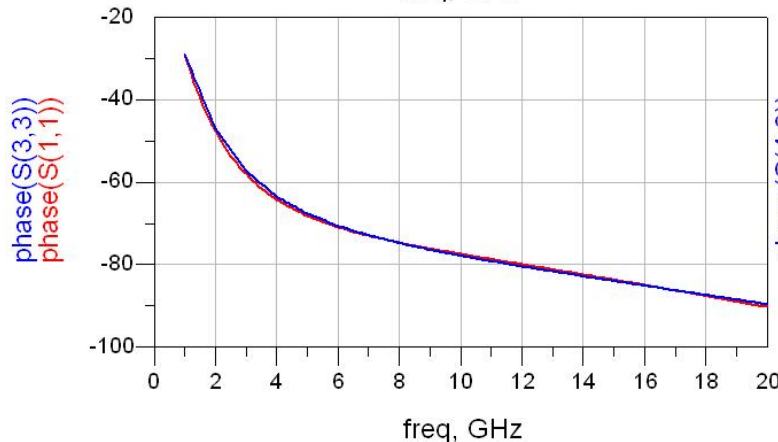
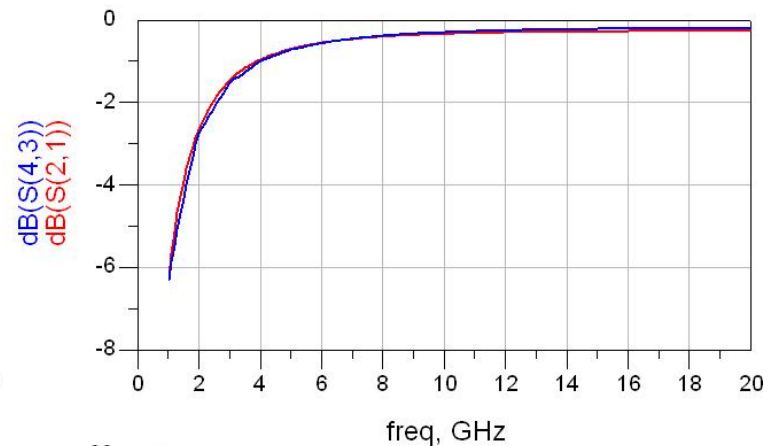
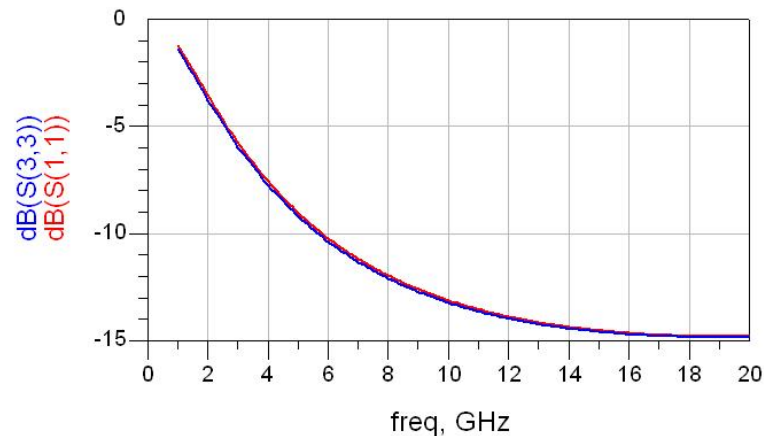
- Optimizare in ADS pentru suprapunerea intre parametrii S pentru schema si parametrii S obtinuti (export) din Sonnet





# Circuit echivalent

- Suprapunerea **trebuie** sa tina cont de faptul ca sunt numere complexe: modul / faza



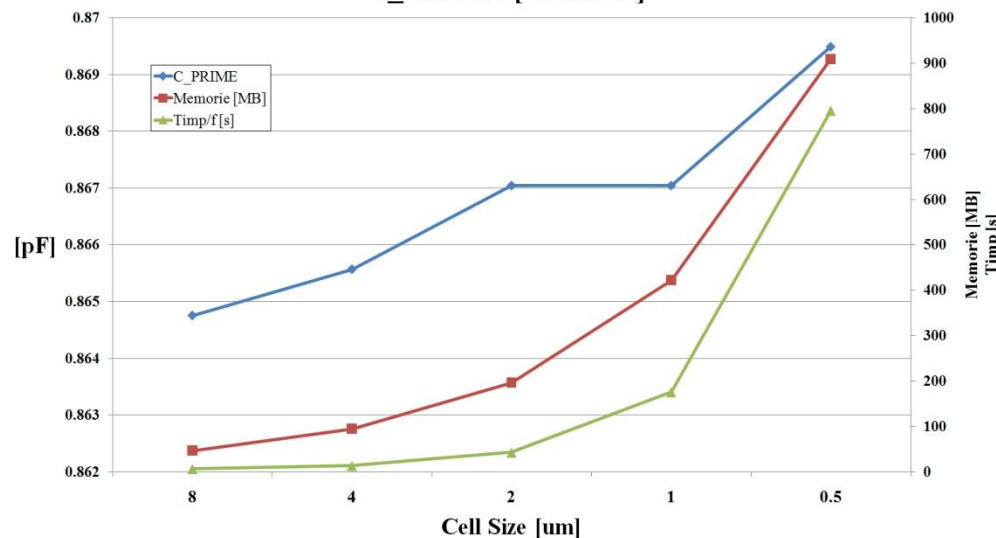
# Convergenta

# Convergenta

- Controlati cum se modifica elementele din schema ( $C_{PRIME}$ ) la modificarea celulei
- Macar 3 pasi necesari pentru nota maxima

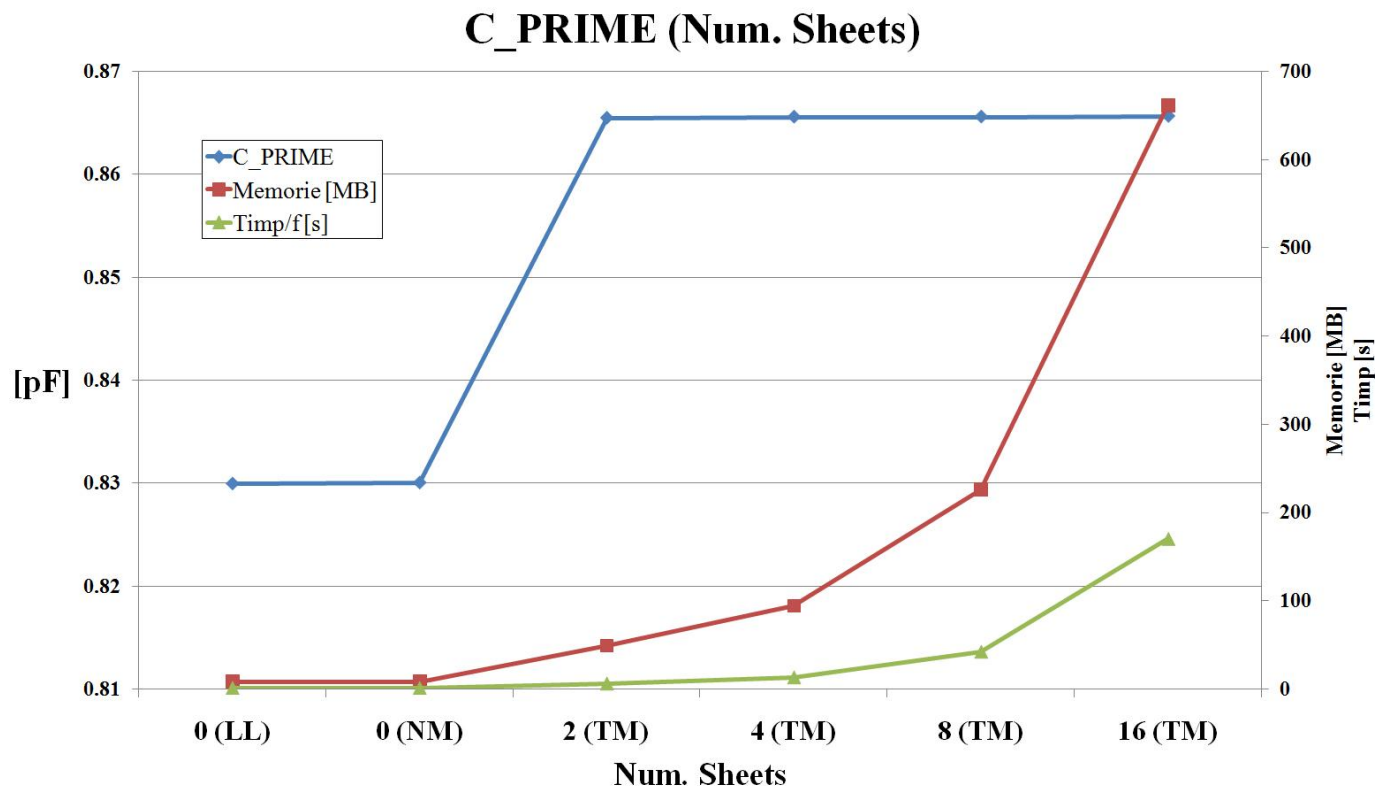
$$\Delta x, \frac{\Delta x}{2}, \frac{\Delta x}{4}, \frac{\Delta x}{8} \dots$$

$C_{PRIME}$  [Cell Size]



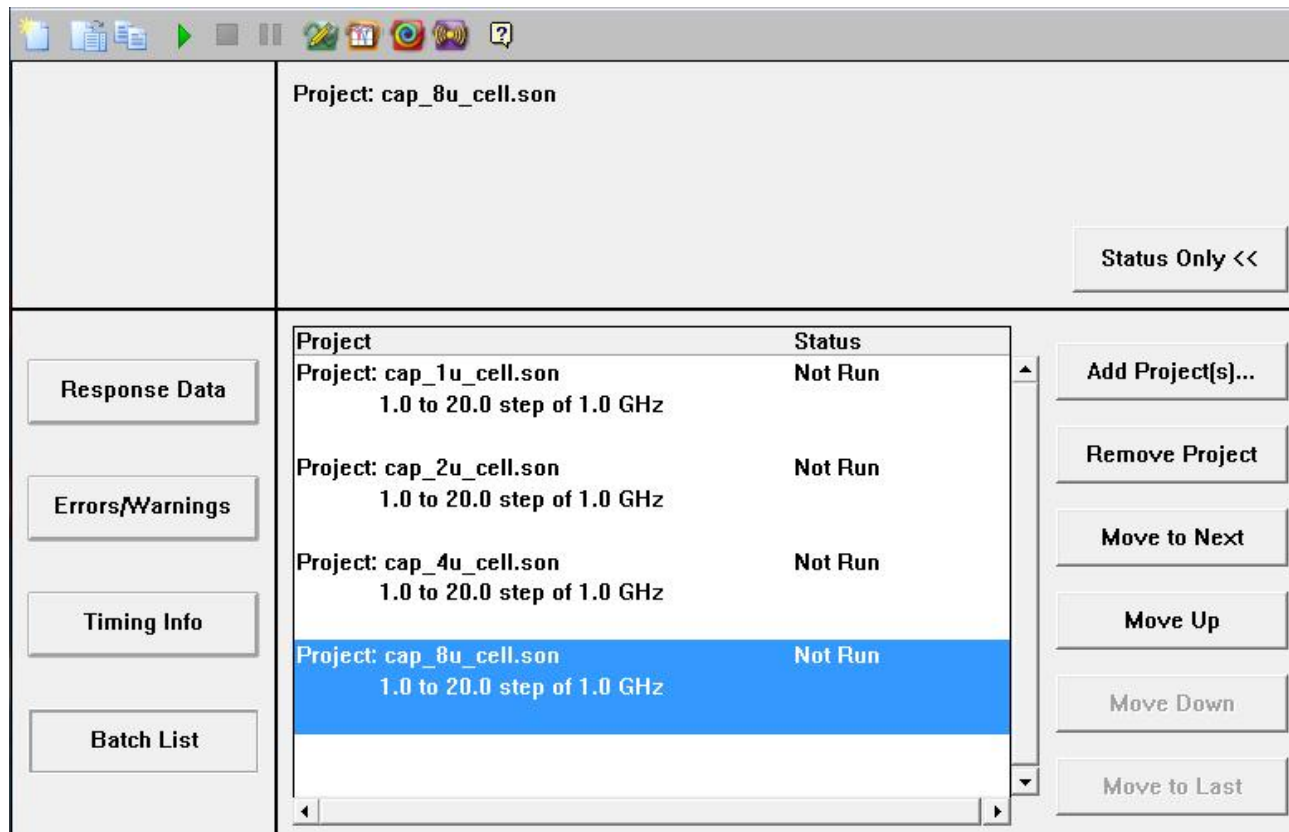
# Exemplu

- Afisat si necesarul de timp/memorie
- Analizele cu detalii suplimentare necesita timp (**de calcul**) semnificativ mai mare (exponential/putere)



# Calcul automat

- Utilizarea “Batch List” pentru rularea succesiva a mai multor simulari cand calculatorul este neutilizat



# Contact

---

- Laboratorul de microunde si optoelectronica
- <http://rf-opto.etti.tuiasi.ro>
- [rdamian@etti.tuiasi.ro](mailto:rdamian@etti.tuiasi.ro)